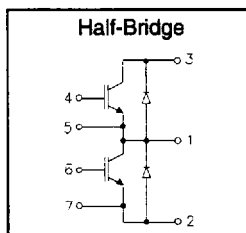


"HALF-BRIDGE" IGBT INT-A-PAK
Low conduction loss IGBT

- Rugged Design
- Simple gate-drive
- Switching-Loss Rating includes all "tail" losses
- Short circuit rated



$$V_{CE} = 1200V$$

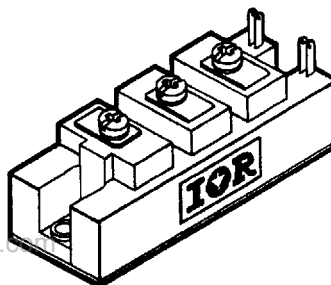
$$I_C = 100A$$

$$V_{CE(ON)} < 2.7V$$

$$t_{sc} > 10\mu s$$

Description

IR's advanced IGBT technology is the key to this line of INT-A-PAK Power Modules. The efficient geometry and unique processing of the IGBT allow higher current densities than comparable bipolar power module transistors, while at the same time requiring the simpler gate-drive of the familiar power MOSFET. These modules are short circuit rated for applications such as motor control requiring this important feature.


INT-A-PAK case
Absolute Maximum Ratings

Parameter	Description	Value	Units
V_{CES}	Continuous collector to emitter voltage	1200	V
$I_C @ T_C = 25^\circ C$	Maximum Continuous collector current	175	A
$I_C @ T_C = 85^\circ C$	Maximum Continuous collector current	100	
$I_C @ T_C = 100^\circ C$	Maximum Continuous collector current	75	
I_{LM}	Peak IGBT switching current	200	
I_{FM}	Peak diode forward switching current (1)	200	V
V_{GE}	Gate to emitter voltage	± 20	
V_{ISOL}	RMS isolation voltage, any terminal to case, $t = 1 \text{ min}$	2500	
$P_D @ T_C = 25^\circ C$	Power dissipation	665	W
T_J	Operating junction temperature range	-40 to 150	$^\circ C$
T_{STG}	Storage temperature range	-40 to 125	

(1) Duration limited by max junction temperature.

IRGTIN100M12

Electrical Characteristics - $T_J = 25^\circ\text{C}$, unless otherwise stated

Parameter	Description	Min	Typ	Max	Units	Test Conditions
BV_{CES}	Collector-to-emitter breakdown voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 3mA$
$V_{CE(ON)}$	Collector-to-emitter voltage	—	2.2	2.7		$V_{GE} = 15V, I_C = 100A$
V_{FM}	Diode forward voltage - maximum	—	1.8	—		$V_{GE} = 15V, I_C = 80A, T_J = 150^\circ\text{C}$
		—	3.2	3.4		$I_F = 100A, V_{GE} = 0V$
		—	2.6	—		$I_F = 100A, V_{GE} = 0V, T_J = 150^\circ\text{C}$
V_{GEth}	Gate threshold voltage	3.0	—	5.5	mV/°C	$I_C = 1mA$
ΔV_{GEth}	Threshold voltage temp. coefficient	—	-11	—		$V_{CE} = V_{GE}, I_C = 1mA$
g_{fe}	Forward transconductance	35	—	70		$V_{CE} = 25V, I_C = 100A$
I_{CES}	Collector-to-emitter leakage current	—	—	3		$V_{GE} = 0V, V_{CE} = 1200V$
I_{GES}	Gate-to-emitter leakage current	—	—	30		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
		—	—	± 3	μA	$V_{GE} = \pm 20V$

Dynamic Characteristics - $T_J = 125^\circ\text{C}$, unless otherwise stated

Parameter	Description	Min	Typ	Max	Units	Test Conditions
E_{on}	Turn-on switching energy	—	0.19	—	mJ/A	$R_G = 6.8\Omega, V_{CC} = 600V$
$E_{off} (1)$	Turn-off switching energy	—	0.36	—		$I_C = 100A, L_S = 100nH$
$E_{ts} (1)$	Total switching energy	—	—	0.60		$V_{GE} = \pm 15V$
$t_{d(on)}$	Turn-on delay time	—	200	250	ns	$R_G = 6.8\Omega, V_{CC} = 600V$
t_r	Rise time	—	200	250		$I_C = 100A$
$t_{d(off)}$	Turn-off delay time	—	125	200		$V_{GE} = \pm 15V$
t_f	Fall time	—	650	—		Resistive load, $T_J = 25^\circ\text{C}$
I_{rr}	Diode peak recovery current	—	50	—	A	$R_G = 6.8\Omega, V_{CC} = 600V$
t_{rr}	Diode recovery time	—	215	—	ns	$I_C = 100A$
Q_{rr}	Diode recovery charge	—	8	—	μC	$V_{GE} = \pm 15V$
Q_{ge}	Gate-to-emitter charge (turn-on)	65	—	260	nC	$V_{CC} = 600V$
Q_{gc}	Gate-to-collector charge (turn-on)	240	—	500		$I_C = 100A$
Q_g	Total gate charge (turn-on)	750	—	1350		$V_{GE} = 15V$
C_{ies}	Input capacitance	15500	—	16500	pF	$V_{GE} = 0V$
C_{oes}	Output capacitance	950	—	1650		$V_{CC} = 30V$
C_{res}	Reverse transfer capacitance	950	—	1650		$f = 1MHz$
t_{sc}	Short circuit withstand time	10	—	—	μs	$V_{CC} = 720V, V_{GE} = \pm 15V$ Min. $R_G = 6.8\Omega, V_{CEP} = 1000V$

(1) Includes tail losses

Thermal and Mechanical Characteristics

Parameter	Description	Typ	Max	Units
R_{thJC} (IGBT)	Thermal resistance, junction to case, each IGBT	—	0.188	$^\circ\text{C/W}$
R_{thJC} (Diode)	Thermal resistance, junction to case, each diode	—	0.205	
R_{thCS} (Module)	Thermal resistance, case to sink	0.041	0.100	
Wt	Weight of module	150	—	g

Refer to Section D - page D-17 for Package Outline11 -INT-A-PAK, New -Half Bridge